

Standard Rectifier

$$V_{RRM} = 1200\text{ V}$$

$$I_{FAV} = 10\text{ A}$$

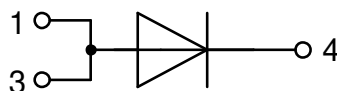
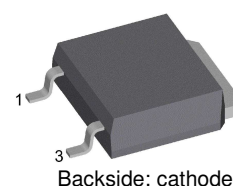
$$V_F = 1.21\text{ V}$$

Single Diode

Part number

DMA10IM1200UZ

Marking on Product: MATMZI



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour
- High commutation robustness
- High surge capability

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: TO-252 (DPak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- High creepage distance between terminals

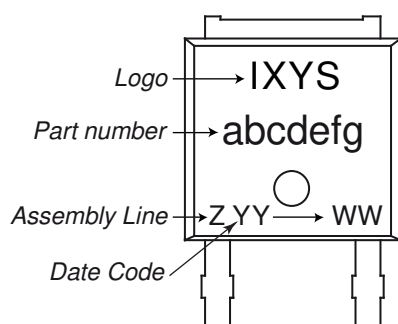
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_R	reverse current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			10	μA
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			0.2	mA
V_F	forward voltage drop	$I_F = 10\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.26	V
		$I_F = 20\text{ A}$				1.53	V
		$I_F = 10\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$			1.21	V
		$I_F = 20\text{ A}$				1.57	V
I_{FAV}	average forward current	$T_C = 150^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}\text{C}$			10	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^{\circ}\text{C}$		0.82	V
r_F	slope resistance					37	m Ω
R_{thJC}	thermal resistance junction to case					1.5	K/W
R_{thCH}	thermal resistance case to heatsink				0.50		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				100	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			120	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			130	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			100	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			110	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			72	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			70	A ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			50	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			50	A ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$			4		pF

Package TO-252 (DPak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			20	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				0.3		g
F_c	mounting force with clip		20		60	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	3.6			mm
$d_{Spb/Apb}$		terminal to backside	3.0			mm

Product Marking



Part description

D = Diode
 M = Standard Rectifier
 A = (up to 1800V)
 10 = Current Rating [A]
 IM = Single Diode
 1200 = Reverse Voltage [V]
 UZ = TO-252AA (DPak) (2HV)

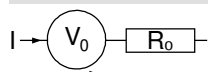
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DMA10IM1200UZ-TRL	MATMZI	Tape & Reel	2500	523229
Alternative	DMA10IM1200UZ-TUB	MATMZI	Tube	70	523574

Similar Part	Package	Voltage class
DMA10IM1600UZ	TO-252AA (DPak) (2HV)	1600

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}\text{C}$



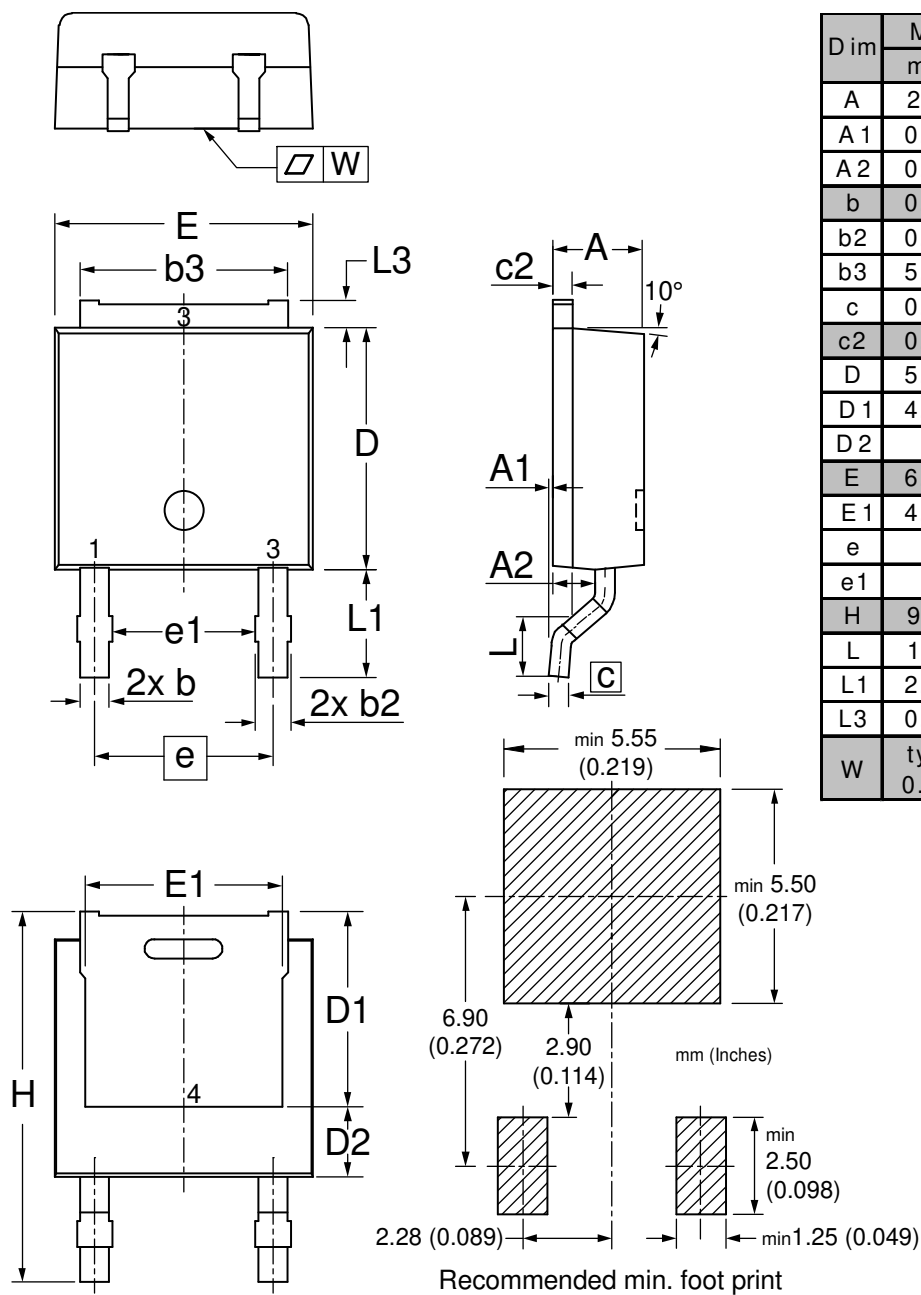
Rectifier

$V_{0\max}$ threshold voltage 0.82

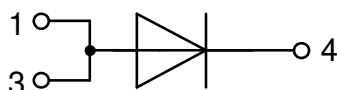
$R_{0\max}$ slope resistance * 34

V

mΩ

Outlines TO-252 (DPak)


Dim	Millimeters		Inches	
	min	max	min	max
A	2.18	2.39	0.086	0.094
A1	0.00	0.13	0.000	0.005
A2	0.97	1.17	0.038	0.046
b	0.64	0.89	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	5.08	5.59	0.200	0.220
c	0.46	0.61	0.018	0.024
c2	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.57	5.21	0.180	0.205
D2	2.03		0.080	
E	6.35	6.73	0.250	0.265
E1	4.32	5.21	0.170	0.205
e	4.57		0.180	
e1	3.62		0.143	
H	9.15	10.34	0.360	0.407
L	1.40	1.78	0.055	0.070
L1	2.54	2.92	0.100	0.115
L3	0.64	1.02	0.025	0.040
W	typ. 0.02	0.040	typ. 0.0008	0.000



Rectifier


Fig. 1 Forward current versus voltage drop per diode



Fig. 2 Surge overload current

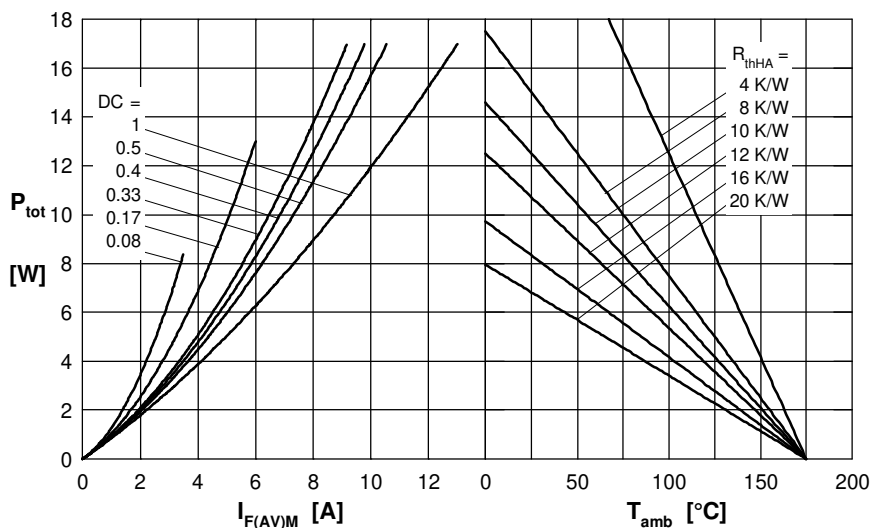

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. direct output current and ambient temperature

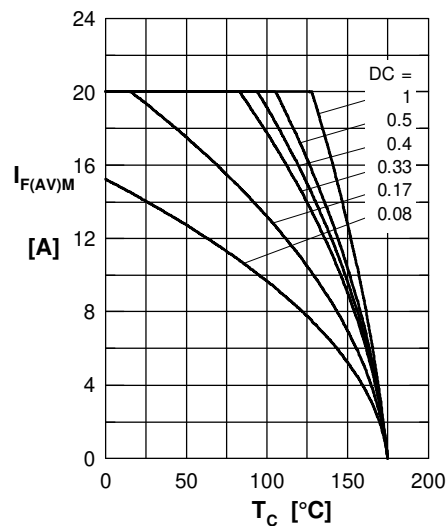


Fig. 5 Max. forward current vs. case temperature



Fig. 6 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.155	0.0005
2	0.332	0.0095
3	0.713	0.17
4	0.3	0.8

